

LIN Transceiver with Voltage Regulator

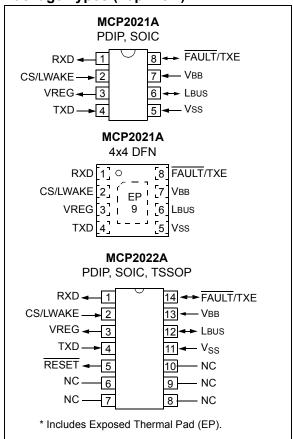
Features

- The MCP2021A/2A is compliant with:
 - LIN Bus Specifications Version 1.3, and 2.x.
 - SAE J2602-2
- · Support Baud Rates up to 20 kBaud
- · 43V Load Dump Protected
- · Maximum Continuous Input Voltage of 30V
- Wide LIN Compliant Supply Voltage, 6.0 18.0V
- Extended Temperature Range: -40 to +125°C
- Interface to PIC[®] EUSART and Standard USARTs
- · Wake-up on LIN Bus Activity or Local Wake Input
- · LIN Bus Pin
 - Internal Pull-up Termination Resistor and Diode for Slave Node
 - Protected Against VBAT Shorts
 - Protected Against Loss of Ground
 - High Current Drive
- · TXD and LIN Bus Dominant Time-out Function
- · Two Low-Power Modes
 - TRANSMITTER OFF Mode: 90 µA (typical)
 - POWER DOWN Mode: 4.5µA (typical)
- Output Indicating Internal RESET State (POR or SLEEP Wake)
- MCP2021A/2A On-chip Voltage Regulator
 - Output Voltage of 5.0V or 3.3V 70 mA Capability withTolerances of ±3% Over Temperature Range
 - Internal Short Circuit Current Limit
 - Only External Filter and Load Capacitors Needed
- · Automatic Thermal Shutdown
- High Electromagnetic Immunity (EMI), Low Electromagnetic Emission (EME)
- Robust ESD Performance: ±15 kV for LBUS and VBB pin (IEC61000-4-2)
- Transient Protection for LBUS and VBB Pins in Automotive Environment (ISO7637)
- Meets Stringent Automotive Design Requirements Including "OEM Hardware Requirements for LIN, CAN and FlexRay Interfaces in Automotive Applications", Version 1.2, March 2011
- Multiple Package Options Including Small 4x4 mm DFN

Description

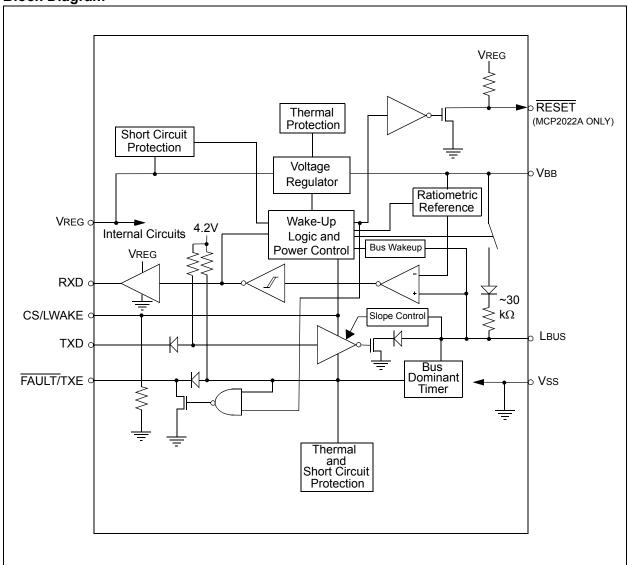
The MCP2021A/2A provides a bidirectional, half-duplex communication physical interface to meet the LIN bus specification Revision 2.1 and SAE J2602-2. The device incorporates a voltage regulator with 5V or 3.3V 70 mA regulated power supply output. The device has been designed to meet the stringent quiescent current requirements of the automotive industry and will survive +43V load dump transients, and double battery jumps.

Package Types (Top View)





Block Diagram



MCP2021A/2A Family Members

| | • | | |
|--------------|--------------------------|--------------------------|-----------|
| Device | Package | Regulator Output Voltage | RESET Pin |
| MCP2021A-500 | 8-PIN DFN, SOIC, PDIP | 5.0V | No |
| MCP2021A-330 | 8-PIN DFN, SOIC, PDIP | 3.3V | No |
| MCP2022A-500 | 14-PIN SOIC, TSSOP, PDIP | 5.0V | Yes |
| MCP2022A-330 | 14-PIN SOIC, TSSOP, PDIP | 3.3V | Yes |

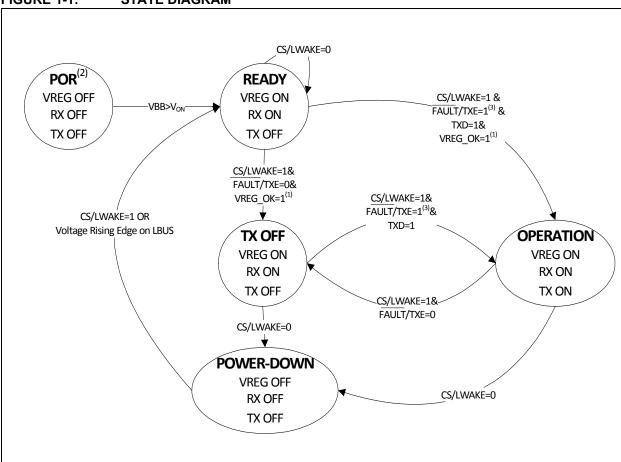
1.0 FUNCTION DESCRIPTION

The MCP2021A/2A provides a physical interface between a microcontroller and a LIN half-duplex bus. It is intended for automotive and industrial applications with serial bus baud rates up to 20 Kbaud. This device will translate the CMOS/TTL logic levels to LIN logic levels, and vice versa. The device offers optimum EMI and ESD performance; it can withstand high voltage on the LIN bus. The device supports two low-power modes to meet automotive industry power consumption requirements. The MCP2021A/2A also provides a +5V or 3.3V 70 mA regulated power output.

1.1 Modes of Operation

The MCP2021A/2A works in five modes: POWER-ON-RESET mode, POWER-DOWN mode, READY mode, OPERATION mode, and TRANSMITTER OFF mode. For an overview of all operational modes, please refer to Table 1-1. For the operational mode transition, please refer to Figure 1-1.

FIGURE 1-1: STATE DIAGRAM



Note 1: VREG OK: Regulator Output Voltage > 0.8VREG_NOM.

- If the voltage on pin VBB falls below V_{OFF}, the device will enter POWER ON RESET mode from all other modes, which is not shown in the figure.
- 3: FAULT/TXE = 1 represents input high and no fault conditions. FAULT/TXE = 0 represents input low or a fault condition, Refer to Table 1-3.

1.1.1 POWER-ON-RESET MODE

Upon application of VBB, or whenever the voltage on VBB is below the threshold of regulator turn off voltage V_{OFF} (typically 4.50V), the device enters POWER-ON-RESET mode (POR). During this mode, the device maintains the digital section in a reset mode and waits

until the voltage on VBB pin rises above the threshold of regulator turn on voltage V_{ON} (typically 5.75V) to enter to the READY mode. In POWER-ON-RESET mode, the LIN physical layer and voltage regulator are disabled, and $\overline{\text{RESET}}$ output (MCP2022A only) is forced to LOW.

1.1.2 READY MODE

The device enters READY mode from POR mode after the voltage on VBB rises above the threshold of regulator turn on voltage V_{ON} or from POWER-DOWN mode when a remote or local wake-up event happens.

Upon entering READY mode, the voltage regulator and receiver section of the transceiver are powered up. The transmitter remains in an off state. The device is ready to receive data but not to transmit. In order to minimize the power consumption, the regulator operates in a reduced power mode. It has a lower GBW product and thus is slower. However, the 70 mA drive capability is unchanged.

The device stays in READY mode until the output of the voltage regulator has stabilized and the CS/LWAKE pin is HIGH ('1').

1.1.3 OPERATION MODE

If VREG is OK (VREG>0.8VREG_NORM), and the CS/LWAKE pin, FAULT/TXE pin and TXD pin are HIGH, the part enters OPERATION mode from either READY or TRANSMITTER OFF mode.

In this mode, all internal modules are operational. The internal pull-up resistor between LBUS and VBB is connected only in this mode.

The device goes into POWER-DOWN mode at the falling edge on CS/LWAKE; or to the TRANSMITTER OFF mode at the falling on FAULT/TXE while CS/LWAKE stays HIGH.

1.1.4 TRANSMITTER OFF MODE

In TRANSMITTER OFF mode, the receiver is enabled but the LBUS transmitter is off. It is a lower power mode.

In order to minimize power consumption, the regulator operates in a reduced power mode. It has a lower GBW product and thus is slower. However the 70 mA drive capability is unchanged.

The transmitter may be re-enabled whenever the FAULT/TXE signal returns high, by removing the internal fault condition and the CPU returning the FAULT/TXE high. The transmitter will not be enabled even if the FAULT/TXE pin is brought high externally, when the internal fault is still present. However, externally forcing the FAULT/TXE high while internal fault is still present should be avoided, since this will induce high current and power dissipation in the FAULT/TXE pin.

The transmitter is also turned off whenever the voltage regulator is unstable or recovering from a fault. This prevents unwanted disruption of the bus during times of uncertain operation.

1.1.5 POWER-DOWN MODE

In POWER-DOWN mode, the transceiver and the voltage regulator are both off. Only the Bus Wake-up section and the CS/LWAKE pin wake-up circuits are in operation. This is the lowest power mode.

If any bus activity (e.g. a BREAK character) occurs during POWER-DOWN mode, the device will immediately enter READY mode and enable the voltage regulator. Then, once the regulator output has stabilized (approximately 0.3 ms to 1.2 ms), it goes to OPERATION mode. Refer to Section 1.1.6 "Remote Wake-up".

The part will also enter READY mode from POWER-DOWN mode, followed by the OPERATION mode, if the CS/LWAKE pin becomes active HIGH ('1').

1.1.6 REMOTE WAKE-UP

The remote wake-up sub module observes the LBUS in order to detect bus activity. In POWER DOWN mode, normal LIN recessive/dominant threshold is disabled, and the LIN bus Wake-Up Voltage Threshold $V_{WK(LBUS)}$ is used to detect bus activities. Bus activity is detected when the voltage on the LBUS falls below the LIN bus Wake-Up Voltage Threshold $V_{WK(LBUS)}$ (approximately 3.5V) for at least t_{BDB} (a typical duration of 80 μs) followed by a rising edge. Such a condition causes the device to leave POWER-DOWN mode.

TABLE 1-1: OVERVIEW OF OPERATIONAL MODES

| State | Transmitter | Receiver | Internal Wake Module | Voltage Regulator | Operation | Comments |
|-----------------|-------------|----------|-------------------------|----------------------|--|---------------------------------------|
| POR | OFF | OFF | OFF | OFF | Transfer to READY mode after VBB>VON | |
| READY | OFF | ON | OFF | ON | If CS/LWAKE high, then proceed to OPERATION or TRANSMITTER OFF mode. | Bus Off state |
| OPERATION | ON | ON | OFF | ON | If CS/LWAKE low level, then Power down If FAULT/TXE low level, then TRANSMITTER-OFF mode | Normal Operation mode |
| POWER DOWN | OFF | OFF | ON Activity Detect | OFF | On LIN bus rising edge or CS/LWAKE high level, go to READY mode. | Lowest Power mode |
| TRANSMITTER-OFF | OFF | ON | OFF | ON | If CS/LWAKE low level, then Power down If FAULT/TXE high, then OPERATION mode | Bus Off state, Lower Power mode |

1.2 Pin Descriptions

Please refer to Table 1-2 for the pinout overview.

1.2.1 VBB

Battery Positive Supply Voltage pin. An external diode is connected in series to prevent the device from being reversely powered (refer to FIGURE 1-9: "Typical Application Circuit").

1.2.2 VREG

Positive Supply Voltage Regulator Output pin. An onchip LDO gives +5.0 or +3.3V 70 mA regulated voltage on this pin.

1.2.3 VSS

Ground pin.

1.2.4 TXD

Transmit data input pin (TTL level, HV compliant, adaptive pull-up). The transmitter reads the data stream on TXD pin and sends it to LIN bus. The LBUS pin is low (dominant) when TXD is low, and high (recessive) when TXD is high.

The Transmit Data Input pin has an internal adaptive pull-up to an internally-generated 4.2V (approximately). When TXD is '0', a weak pull-up (~900 k Ω) is used to reduce current. When TXD is '1', a stronger pull-up (~300 k Ω) is used to maintain the logic level. A series reverse-blocking diode allows applying TXD input voltages greater than the internally generated 4.2V and renders TXD pin HV compliant up to 30V (see block diagram).

1.2.5 RXD

Receive Data Output pin. The RXD pin is a standard CMOS output pin and it follows the state of the LBUS pin.

1.2.6 LBUS

LIN Bus pin. LBUS is a bidirectional LIN bus Interface pin and is controlled by the signal TXD. It has an open collector output with a current limitation. To reduce ElectroMagnetic Emission, the slopes during signal changes are controlled, and the LBUS pin has corner-rounding control for both falling and rising edges.

The internal LIN receiver observes the activities on the LIN bus, and generates the output signal RXD that follows the state of the LBUS. A 1st degree 160 kHz, low-pass input filter optimizes ElectroMagnetic immunity.

1.2.7 CS/LWAKE

Chip Select and Local Wake-up Input pin (TTL level, high voltage tolerant). This pin controls the device state transition. Refer to **FIGURE 1-1: "State Diagram"**.

If CS/LWAKE = 1, the device can work in OPERATION $\underline{\text{mode}}$ (FAULT/TXE = 1) or TRANSMITTER OFF mode (FAULT/TXE = 0).

If CS/LWAKE = 0, the device can work in POWER-DOWN mode or READY mode.

An internal pull-down resistor will keep the CS/LWAKE pin low to ensure that no disruptive data will be present on the bus while the microcontroller is executing a Power-on Reset and I/O initialization sequence. When CS/LWAKE is '1', a weak pull-down (~600 k Ω) is used to reduce current. When CS/LWAKE is '0' a stronger pull-down (~300 k Ω) is used to maintain the logic level.

This pin may also be used as a local wake-up input (See FIGURE 1-9: "Typical Application Circuit"). The microcontroller will set the I/O pin to control the CS/LWAKE. An external switch, or other source, can then wake-up both the transceiver and the microcontroller.

Note: CS/LWAKE should NOT be tied directly to the VREG pin as this could force the MCP2021A/2A into Operation Mode before the microcontroller is initialized.

1.2.8 FAULT/TXE

Fault Detect Output/Transmitter Enable Input pin. The output section is HV tolerant open drain (up to 30V). The input section is identical with the TXD section (TTL level, HV compliant, adaptive pull-up). Internal adaptive pull-up maintains this input high '1' if the pin is floating. Its state is defined as shown in TABLE 1-3: "FAULT/TXE Truth Table". The device is placed in TRANSMITTER OFF mode whenever this pin is LOW ('0'), either from an internal fault condition or by external drive.

If CS/LWAKE is HIGH ('1'), the FAULT/TXE signals a mismatch between the TXD input and the LBUs level. This can be used to detect a bus contention. Since the bus exhibits a propagation delay, the sampling of the internal compare is debounced to eliminate false faults.

After the device wakes up, the FAULT/TXE indicates what wakes the device if CS/LWAKE remains LOW ('0') (refer Table 1-3).

The FAULT/TXE pin sampled at a rate faster than every 10 µs.

1.2.9 RESET (MCP2022A ONLY)

RESET OUTPUT pin. This pin is open drain with ~90 k Ω pull-up to VREG. It indicates the internal voltage has reached a valid, stable level. As long as the internal voltage is valid (above 0.8 VREG), this pin will remain HIGH ('1'); otherwise the RESET pin switches to LOW ('0').

TABLE 1-2: PINOUT OVERVIEW

| PIN Name | PIN N | umber | DIN Type | Function | | |
|-----------|----------|----------|------------------------|--|--|--|
| PIN Name | MCP2021A | MCP2022A | PIN Type | Function | | |
| VREG | 3 | 3 | Output | Voltage Regulator Output | | |
| VSS | 5 | 11 | Power | Ground | | |
| VBB | 7 | 13 | Power | Battery | | |
| TXD | 4 | 4 | Input, HV-tolerant | Transmit Data Input | | |
| RXD | 1 | 1 | Output | Receive Data Output | | |
| LBUS | 6 | 12 | I/O, HV | LIN Bus | | |
| CS/LWAKE | 2 | 2 | TTL Input, HV-tolerant | Chip Select and Local Wake-up Input | | |
| FAULT/TXE | 8 | 14 | I/O, HV-tolerant | Fault Detect Output/Transmitter Enable Input | | |
| RESET | - | 5 | Output | Reset Output | | |

TABLE 1-3: FAULT/TXE TRUTH TABLE

| TVD | DVD | I IN THE | Th | FAUL | T/TXE | |
|-----------|------------|----------------|---------------------|---------------------------------|-------------|--|
| TXD In | RXD Out | LIN BUS I/O | Thermal Override | External Driven Input Output | | Definition |
| | | | | CS | = 1 | |
| L | Н | Vвв | OFF | Н | L | FAULT, TXD driven low, LIN BUS shorted to VBB (Note 1), or LBUS/TXD permanent dominant detected, and Transmit time-out shutdown. |
| Н | Н | VBB | OFF | Н | Н | ОК |
| L | L | GND | OFF | Н | Н | ОК |
| Н | L | GND | OFF | Н | Н | OK , data is being received from the LIN BUS |
| Х | Х | VBB | ON | Н | L | FAULT, Transceiver in thermal shutdown |
| Х | Х | Vвв | х | L | Х | NO FAULT, the CPU is commanding the transceiver to turn off the transmitter driver |
| | | | | CS = 0 afte | r a wake-up | |
| х | х | х | х | Х | L | Wake-up from LIN bus activity |
| Х | Х | х | х | Х | Н | Wake-up from POR |

Legend: x = don't care

Note 1: The FAULT/TXE is valid after approximately 25 μs after TXD falling edge. This is to eliminate false fault reporting during bus propagation delays.

1.3 Fail-Safe Features

1.3.1 GENERAL FAIL-SAFE FEATURES

- An internal pull-down resistor on CS/LWAKE pin disables the transmitter if the pin is floating.
- An internal pull-up resistor on the TXD pin places TXD in HIGH thus the LBUS in recessive if TXD pin is floating.
- High-impedance and low-leakage current on LBUS during loss of power or ground.
- The current limit on LBUS protects the transceiver from being damaged if the pin is shorted to VBB.

1.3.2 THERMAL PROTECTION

The thermal protection circuit monitors the die temperature and is able to shut down the LIN transmitter and voltage regulator.

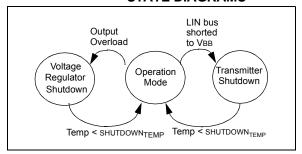
There are three causes for a thermal overload. A thermal shut down can be triggered by any one, or a combination of, the following thermal overload conditions.

- · Voltage regulator overload
- LIN bus output overload
- Increase in die temperature due to increase in environment temperature

The recovery time from the thermal shutdown is equal to adequate cooling time.

Driving the TXD and checking the RXD pin make it possible to determine whether there is a bus contention (TXD = high, RXD = low) or a thermal overload condition (TXD = low, RXD = high).

FIGURE 1-2: THERMAL SHUTDOWN STATE DIAGRAMS



1.3.3 TXD/LBUS TIME-OUT TIMER

The LIN bus can be driven to a dominant level either from the TXD pin or externally. An internal timer deactivates the LBUS transmitter if a dominant status (LOW) on the LIN bus lasts longer than Bus Dominant Time-out Time t_{TO(LIN)} (approximately 20 milliseconds). At the same time, RXD output is put in recessive (HIGH), FAULT/TXE is also driven to LOW, and the internal LIN pull-up resistor is disconnected. The timer is reset on any recessive LBUS status or POR mode. The recessive status on LBUS can be caused either by the bus being externally pulled up or by the TXD pin being returned high.

1.4 Internal Voltage Regulator

The MCP2021A/2A has a positive regulator capable of supplying +5.00 or +3.30 VDC $\pm 3\%$ at up to 70 mA of load current over the entire operating temperature range of -40°C to +125°C. The regulator uses a LDO design, is short-circuit-protected and will turn the regulator output off if its output falls below the Shutdown Voltage Threshold V_{SD}.

With a load current of 70 mA, the minimum input to output voltage differential required for the output to remain in regulation is typically +0.5V (+1V maximum over the full operating temperature range). Quiescent current is less than 100 μ A with a full 70 mA load current when the input to output voltage differential is greater than +3.00V.

Regarding the correlation between VBB, VREG and IDD, please refer to Figure 1-6 and Figure 1-7. When the input voltage (VBB) drops below the differential needed to provide stable regulation, the voltage regulator output VREG will track the input down to approximately VOFF. The regulator will turn off the output at this point. This will allow PIC® microcontrollers, with internal POR circuits, to generate a clean arming of the Power-on Reset trip point. The MCP2021A/2A will then monitor VBB and turn on the regulator when VBB is above the threshold of regulator turn on voltage VON.

In Power-down mode, the VBB monitor is turned off.

Under specific ambient temperature and battery voltage range, the voltage regulator can output as high as 150mA current. For current load capability of the voltage regulator, refer Figure 1-4 and Figure 1-5.

Note: The regulator overload current limit is approximately 250 mA. The regulator output voltage V_{REG} is monitored. If output voltage V_{REG} is lower than V_{SD} , the voltage regulator will turn off. After a recovery time of about 3mS, the V_{REG} will be checked again. If there is no short circuit ($V_{REG} > V_{SD}$), then the voltage regulator remains on.

The regulator requires an external output bypass capacitor for stability. See Figure 2-1 for correct capacity and ESR for stable operation.

FIGURE 1-3: VOLTAGE REGULATOR BLOCK DIAGRAM

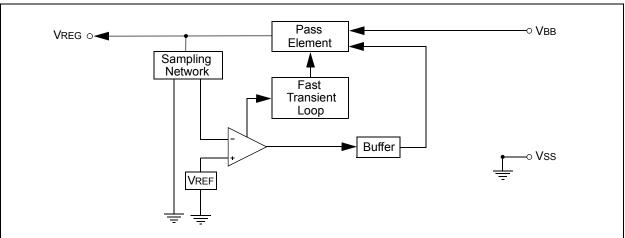


FIGURE 1-4: $5.0V V_{REG} VS. I_{REG} AT VBB = 12V$

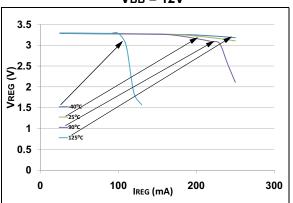
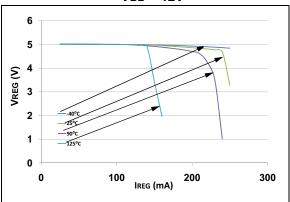
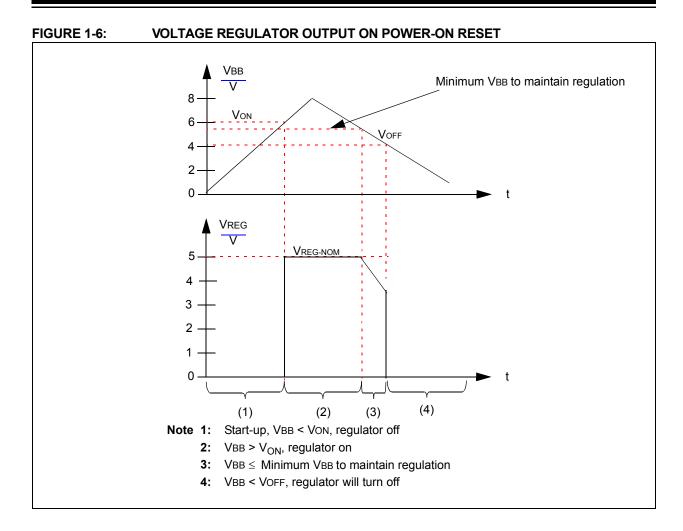
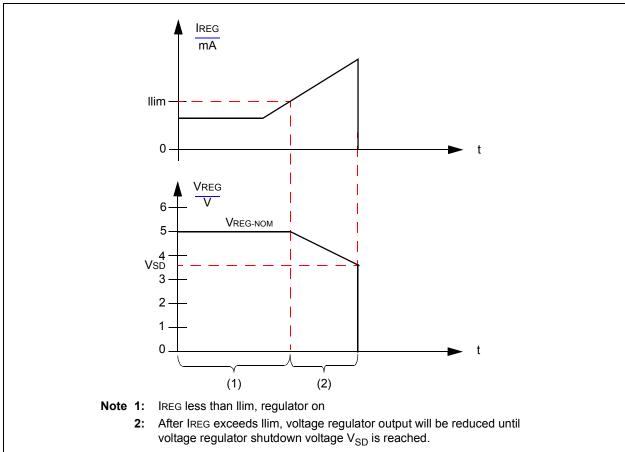


FIGURE 1-5: 3.3V V_{REG} VS. I_{REG} AT $V_{BB} = 12V$









1.5 Optional External Protection

1.5.1 REVERSE BATTERY PROTECTION

An external reverse-battery-blocking diode should be used to provide polarity protection (see Figure 1-9).

1.5.2 TRANSIENT VOLTAGE PROTECTION (LOAD DUMP)

An external 43V transient suppressor (TVS) diode, between VBB and ground, with a transient protection resistor (RTP) in series with the battery supply and the VBB pin protects the device from power transients and ESD events greater than 43V (see Figure 1-9). The maximum value for the RTP protection resistor depends upon two parameters: the minimum voltage the part will start at, and the impacts of this RTP resistor on the VBB value, thus on the Bus recessive level and slopes.

This leads to a set of three equations to fullfil.

Equation 1-1 provides a max RTP value according to the minimum battery voltage the user wants.

Equation 1-2 provides a max RTP value according to the maximum error on the recessive level, thus VBB, since the part uses VBB as the reference value for the recessive level.

Equation 1-3 provides a max RTP value according to the maximum relative variation the user can accept on the slope when IREG varies.

Since both Equation 1-1 and Equation 1-2 must be fulfilled, the maximum allowed value for RTP is thus the smaller of the two values found when solving Equation 1-1 and Equation 1-2.

Usually Equation 1-1 gives the higher constraint (smaller value) for RTP as shown in the following example where VBATmin is 8V.

However, the user needs to check that the value found with Equation 1-1 fulfills Equation 1-2 and Equation 1-3 as well.

While this protection is optional, it should be considered as good engineering practice.

EQUATION 1-1:

$$R_{TP} \leq \frac{V_{BATmin} - 5.5 V}{250 \, mA}$$

$$5.5V = V_{OFF} + 1.0V$$

250 mA is the peak current at power-on when VBB =5.5V

Assume VBATMIN = 8V. Equation 1-1 shows 10Ω .

EQUATION 1-2:

 $R_{TP} \leftarrow \Delta V_{RECCESSIVE} / I_{REGMAX}.$ $\Delta V_{RECCESSIVE}$ is the maximum variation tolerated on the recessive level

Assume ΔV RECCESSIVE = 1V and IREGMAX = 50 mA Equation 1-2 shows 20Ω .

EQUATION 1-3:

$$R_{TP} \leq \frac{\Delta Slope \times (V_{BATmin} - 1\,V)}{I_{regmax}}$$

ΔSlope is the maximum variation tolerated on the slope level and IREGMAX is the maximum current the regulator will provide to the load.

VBATmin>VOFF + 1.0V.

Assume Δ Slope = 15%, VBATMIN = 8V and IREGMAX = 50 mA. Equation 1-2 shows 20 Ω .

1.5.3 **CBAT CAP**

Selecting CBAT = 10* CREG is recommended, however, this leads to a high value cap. Lower values for CBAT cap can be used with respect to some rules. In any case, the voltage at the V_{BB} pin should remain above V_{OFF} when the device is turned on.

The current peak at start-up (due to the fast charge of the CREG and CBAT capacitors) may induce a significant drop on the VBB pin. This drop is proportional to the impedance of the VBAT connection (see Figure 1-9).

Assume that the VBAT connection is mainly inductive and resistive, and that the customer knows the resistive and inductive values of the connection.

The following formula gives an indication of the minimum value the customer should use for CBAT:

EQUATION 1-4:

$$\frac{C_{BAT}}{C_{REG}} = \sqrt{\frac{100L^2 + R_{tot}^2}{1 + L^2 + \frac{R_{tot}^2}{100}}}$$
where L is in mH and R_{tot} in Ω .
$$R_{tot} = R_{line} + R_{TP}.$$

Equation 1-4 allows lower CBAT/CREG values than the 10* ratio we recommend.

Let's assume that we have a good quality connection with RTOT = 0.1Ω and L = 0.1 mH.

Solving the equation gives CBAT/CREG = 1.

If we increase RTOT up to $1\Omega,$ the result becomes CBAT/ CREG = 1.4.

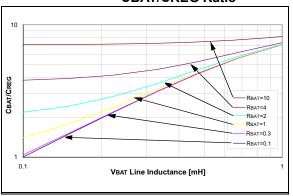
But if the connection is highly resistive or highly inductive (poor connection), the CBAT/CREG ratio greatly increases.

Highly inductive connection: Let's have RTOT = 0.1Ω and L = 1 mH: the CBAT/CREG ratio increases to 7!

Highly resistive connection: Let's have RTOT = 10Ω and L = 0.1 mH: again the CBAT/CREG ratio increases to 7!

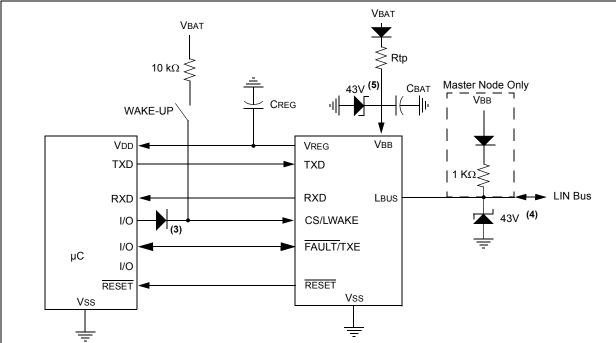
Figure 1-8 shows the minimum recommended CBAT/ CREG ratio as a function of the impedance of the VBAT connection.

FIGURE 1-8: Minimum Recommended CBAT/CREG Ratio



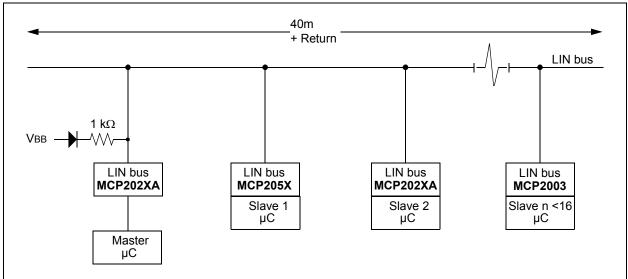
1.6 Typical Applications

FIGURE 1-9: TYPICAL APPLICATION CIRCUIT



- Note 1: CREG, the load capacitor, should be ceramic or tantalum rated for extended temperatures, 1.0- $22 \mu F$. See Figure 2-1 for selecting the correct ESR.
 - 2: CBAT is the filter capacitor for the external voltage supply. Typically 10 * CREG, with no ESR restriction. See Figure 1-8 to select the minimum recommended value for CBAT. The RTP value is added to the line resistance.
 - 3: This diode is only needed if CS/LWAKE is connected to VBAT supply.
 - 4: Transient suppressor diode. Vclamp L = 43V.
 - 5: This component is for additional load dump protection.

FIGURE 1-10: TYPICAL LIN NETWORK CONFIGURATION



1.7 ICSP™ Considerations

The following should be considered when the MCP2021A/2A is connected to pins supporting in-circuit programming:

- Power used for programming the microcontroller can be supplied from the programmer, or from the MCP2021A/2A.
- The voltage on the pin VREG should not exceed the maximum value of VREG in Section 2.3 "DC Specifications".

NOTES:

2.0 ELECTRICAL CHARACTERISTICS

2.1 Absolute Maximum Ratings†

| VIN DC Voltage on RXD, and RESET | 0.3V to VREG+0.3 |
|---|------------------|
| VIN DC Voltage on TXD, CS/LWAKE, FAULT/TXE | |
| VBB Battery Voltage, continuous, non-operating (Note 1) | 0.3 to +40V |
| VBB Battery Voltage, non-operating (LIN bus recessive, no regulator load, t < 60s) (Note 2) | 0.3 to +43V |
| VBB Battery Voltage, transient ISO 7637 Test 1 | 100V |
| VBB Battery Voltage, transient ISO 7637 Test 2a | +75V |
| VBB Battery Voltage, transient ISO 7637 Test 3a | 150V |
| VBB Battery Voltage, transient ISO 7637 Test 3b | +100V |
| VLBUS Bus Voltage, continuous | 18 to +30V |
| VLBUS Bus Voltage, transient (Note 3) | 27 to +43V |
| ILBUS Bus Short Circuit Current Limit | 200 mA |
| ESD protection on LIN, VBB (IEC 61000-4-2) (Note 4) | ±15 KV |
| ESD protection on LIN, VBB (Human Body Model) (Note 5) | ±8 KV |
| ESD protection on all other pins (Human Body Model) (Note 5) | ±4 KV |
| ESD protection on all pins (Charge Device Model) (Note 6) | ±1500V |
| ESD protection on all pins (Machine Model) (Note 7) | ±200V |
| Maximum Junction Temperature | 150°C |
| Storage Temperature | 65 to +150°C |

- Note 1: LIN 2.x compliant specification.
 - 2: SAE J2602-2 compliant specification.
 - **3:** ISO 7637/1 load dump compliant (t < 500 ms).
 - 4: According to IEC 61000-4-2, 330 ohm, 150 pF and Transceiver EMC Test Specifications [2] to [4].
 - 5: According to AEC-Q100-002 / JESD22-A114.
 - 6: According to AEC-Q100-011B.
 - **7:** According to AEC-Q100-003 / JESD22-A115.

† NOTICE: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

2.2 Nomenclature Used in This Document

Some terms and names used in this data sheet deviate from those referred to in the LIN specifications. Equivalent values are shown below.

| LIN 2.1 Name | Term used in the following tables | |
|--------------|-----------------------------------|------------------------------|
| VBAT | not used | ECU operating voltage |
| Vsup | Vвв | Supply voltage at device pin |
| VBUS_LIM | Isc | Current limit of Driver |
| VBUSREC | Vih(LBUS) | Recessive state |
| VBUSDOM | VIL(LBUS) | Dominant state |

2.3 DC Specifications

| DC Specifications | Electrical Char Unless otherwis VBB = 6.0V to 19 TA = -40°C to +4 | e indicated, a 8.0V | ll limits ar | e specified | for: | |
|---|--|------------------------|--------------|--------------|-------|--|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Conditions |
| Power | | | | | | |
| VBB Quiescent Operating Current | IBBQ | _ | | 200 | μA | IOUT = 0 mA, LBUS recessive V _{REG} = 5.0V |
| | | _ | | 200 | μA | IOUT = 0 mA, LBUS recessive V _{REG} = 3.3V |
| VBB READY Current | IBBRD | _ | _ | 100 | μА | IOUT = 0 mA, LBUS recessive V _{REG} = 5.0V |
| | | _ | _ | 100 | μA | IOUT = 0 mA, LBUS recessive V _{REG} = 3.3V |
| VBB Transmitter-off Current | Іввто | _ | | 100 | μА | With voltage regulator on, transmitter off, receiver on, FAULT/TXE = VIL, CS = VIH, V _{REG} = 5.0V |
| | | _ | | 100 | μА | With voltage regulator on, transmitter off, receiver on, FAULT/TXE = VIL, CS = VIH, V _{REG} = 3.3V |
| VBB Power-down Current | Іввро | _ | 4.5 | 8 | μА | With voltage regulator powered-off, receiver on and transmitter off, FAULT/TXE = VIH, TXD = VIH, CS = VIL) |
| VBB Current with Vss Floating | IBBNOGND | -1 | _ | 1 | mA | VBB = 12V, GND to VBB, VLIN = 0-18V |
| Microcontroller Interface | | | | | | |
| High Level Input Voltage (Txp, FAULT/TXE) | ViH | 2.0 | _ | VREG +0.3 | V | |
| Low Level Input Voltage (TxD, FAULT/TXE) | VIL | -0.3 | | 0.8 | V | |
| High Level Input Current (TXD, FAULT/TXE) | ІІН | -2.5 | _ | 0.4 | μA | Input voltage = 4.0V. ~800 kΩ internal adaptive pull-up |
| Low Level Input Current (TXD, FAULT/TXE) | lıL | -10 | _ | _ | μA | Input voltage = 0.5V. ~800 kΩ internal adaptive pull-up |
| High Level Input Voltage (CS/LWAKE) | ViH | 2.0 | _ | VBB | V | Through a current-limiting resistor |
| Low Level Input Voltage (CS/LWAKE) | VIL | -0.3 | _ | 0.8 | V | |
| High Level Input Current (CS/LWAKE) | lін | _ | _ | 8.0 | μА | Input voltage = $0.8VREG$ ~1.3 M Ω internal pulldown to Vss |

2.3 DC Specifications (Continued)

| DC Specifications | Electrical Char Unless otherwis VBB = 6.0V to 18 TA = -40°C to +2 | e indicated, all 8.0V | limits a | re specified fo | or: | |
|--------------------------------------|--|--------------------------|----------|-----------------|-------|--|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Conditions |
| Low Level Input Current (CS/LWAKE) | lıL | _ | | 5.0 | μA | Input voltage = 0.2VREG \sim 1.3 M Ω internal pulldown to Vss |
| Low Level Output Voltage (RXD) | Volrxd | _ | | 0.2VREG | V | IOL = 2 mA |
| High Level Output Voltage (RXD) | VOHRXD | 0.8VREG | | _ | V | Iон = 2 mA |
| Low Level Output Voltage (FAULT/TXE) | VOLOD | _ | | 1.0 | V | IOL = 4 mA |
| Low Level Output Voltage (RESET) | Volrst | _ | | 1.0 | V | IOL = 4 mA |

2.3 DC Specifications (Continued)

| DC Specifications | Unless otherwis | Electrical Characteristics: Unless otherwise indicated, all limits are specified for: VBB = 6.0V to 18.0V TA = -40°C to +125°C | | | | | | | |
|--|-----------------------|--|------------|-----------|-------|--|--|--|--|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Conditions | | | |
| Bus Interface (DC specifica | ations are for a \ | V вв range of 6 | .0 to 1 | 8.0V) | | | | | |
| High Level Input Voltage | VIH(LBUS) | 0.6 Vвв | _ | ı | V | Recessive state | | | |
| Low Level Input Voltage | VIL(LBUS) | -8 | | 0.4 VBB | V | Dominant state | | | |
| Input Hysteresis | VHYS | | _ | 0.175 VBB | V | VIH(LBUS) – VIL(LBUS) | | | |
| Low Level Output Current | IOL(LBUS) | 40 | _ | 200 | mA | Output voltage = 0.1 VBB, VBB = 12V | | | |
| Pull-up Current on Input | IPU(LBUS) | -180 | _ | -72 | μA | ~30 kΩ internal pull-up @ VIH (LBUS) = 0.7 VBB, VBB=12V | | | |
| Short Circuit Current Limit | Isc | 50 | _ | 200 | mA | (Note 1) | | | |
| High Level Output Voltage | Voh(LBUS) | 0.8 VBB | | VBB | V | | | | |
| Driver Dominant Voltage | V_LOSUP | _ | _ | 1.1 | V | VBB = 7.3V, RLOAD = $1000Ω$ | | | |
| Driver Dominant Voltage | V_HISUP | _ | _ | 1.2 | V | VBB = 18V, RLOAD = 1000Ω | | | |
| Input Leakage Current (at the receiver during dominant bus level) | IBUS_PAS_DOM | -1 | _ | _ | mA | Driver off, VBUS = 0V, VBB = 12V | | | |
| Input Leakage Current (at the receiver during recessive bus level) | IBUS_PAS_REC | -20 | _ | 20 | μA | Driver off, 8V < V _{BB} < 18V 8V < V _{BUS} < 18V V _{BUS} ≥ V _{BB} | | | |
| Leakage Current (disconnected from ground) | IBUS_NO_GND | -10 | _ | +10 | μA | GNDDEVICE = VBB, 0V < VBUS < 18V, VBB = 12V | | | |
| Leakage Current (disconnected from VBB) | IBUS_NO_PWR | -10 | _ | +10 | μA | VBB = GND, 0 < VBUS < 18V | | | |
| Receiver Center Voltage | VBUS_CNT | 0.475 VBB | 0.5 VBB | 0.525 VBB | V | VBUS_CNT = (VIL (LBUS) + VIH (LBUS))/2 | | | |
| Slave Termination | RSLAVE | 20 | 30 | 47 | kΩ | (Note 2) | | | |
| Capacitance of slave node | CSLAVE | | | 50 | pF | (Note 2) | | | |
| Wake-Up Voltage Threshold on LIN Bus | V _{WK(LBUS)} | _ | _ | 3.4 | V | Wake up from POWER- DOWN mode (Note 3) | | | |

Note 1: Internal current limited. 2.0 ms maximum recovery time (RLBUS = 0Ω , TX = 0, VLBUS = VBB).

^{2:} For design guidance only, not tested.

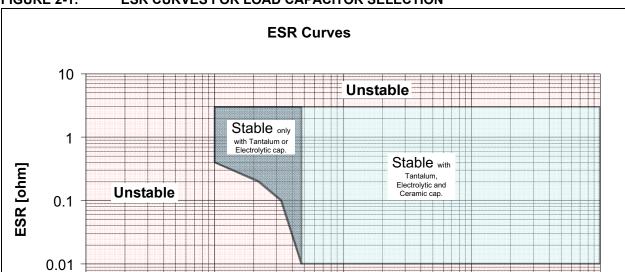
^{3:} In POWER DOWN mode, normal LIN recessive/dominant threshold is disabled; V_{WK(LBUS)} is used to detect bus activities.

2.3 DC Specification (Continued)

| DC Specifications | Unless otherwis VBB = 6.0V to 1 TA = -40°C to +2 CLOADREG = 10 | se indicated, 8.0V 125°C | all limits ar | e specified | for: | |
|----------------------------------|---|--------------------------------|---------------|-------------|---------------|---|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Conditions |
| Voltage Regulator - 5.0V | | | | | | |
| Output Voltage Range | VREG | 4.85 | 5.00 | 5.15 | V | 0 mA < Iout < 70 mA |
| Line Regulation | ΔVουτ1 | _ | 10 | 50 | mV | IOUT = 1 mA, 6.0V < VBB < 18V |
| Load Regulation | ΔVουτ2 | _ | 10 | 50 | mV | 5 mA < IOUT <70 mA 6.0V < VBB < 12V |
| Power Supply Ripple Reject | PSRR | _ | _ | 50 | dB | 1 VPP @10-20 kHz ILOAD = 20 mA |
| Output Noise Voltage | eN | _ | _ | 100 | μVRMS | 10 Hz – 40 MHz CFILTER = 10 μf, CBP = 0.1 μf, ILOAD = 20 mA |
| Shutdown Voltage Threshold | V _{SD} | 3.5 | | 4.0 | V | See Figure 1-7 (Note 1) |
| Input Voltage to Turn Off Output | V _{OFF} | 3.9 | | 4.5 | V | |
| Input Voltage to Turn On Output | V _{ON} | 5.25 | | 6.0 | V | |
| Voltage Regulator - 3.3V | | | | | * | |
| Output Voltage | VREG | 3.20 | 3.30 | 3.40 | V | 0 mA < Iout < 70 mA |
| Line Regulation | ΔVουτ1 | _ | 10 | 50 | mV | IOUT = 1 mA, 6.0V < VBB < 18V |
| Load Regulation | ΔVουτ2 | _ | 10 | 50 | mV | 5 mA < IOUT < 70 mA, 6.0V < VBB < 12V |
| Power Supply Ripple Reject | PSRR | _ | | 50 | dB | 1 VPP @10-20 kHz , ILOAD = 20 mA |
| Output Noise Voltage | eN | _ | _ | 100 | µVRMS /√Hz | 10 Hz – 40 MHz CFILTER = 10 μf, CBP = 0.1 μf, ILOAD = 20 mA |
| Shutdown Voltage | V _{SD} | 2.5 | _ | 2.7 | V | See Figure 1-7 (Note 1) |
| Input Voltage to Turn Off Output | V _{OFF} | 3.9 | | 4.5 | V | |
| Input Voltage to Turn On Output | V _{ON} | 5.25 | | 6 | V | |
| Note 1: For design guid | dance only, not te | sted. | | | | |

0.001 +

0.1



Unstable

100

1000

10

Load Capacitor [uF]

FIGURE 2-1: ESR CURVES FOR LOAD CAPACITOR SELECTION

1

2.4 AC Specification

| AC CHARACTERISTICS | VBB = 6.0V to | 18.0V; TA | \ = -40°C to | +125°C | | |
|--|----------------------|------------|--------------|------------|----------|--|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Test Conditions |
| Bus Interface - Constant Slo | pe Time Para | ameters (C | OC specific | ations are | for a VE | B range of 6.0 to 18.0V) |
| Slope rising and falling edges | tslope | 3.5 | _ | 22.5 | μs | 7.3V <= VBB <= 18V |
| Propagation Delay of Transmitter | ttranspd | _ | _ | 5.0 | μs | ttranspd = max (ttranspdr or ttranspdf) |
| Propagation Delay of Receiver | trecpd | _ | _ | 6.0 | μs | trecpd = max (trecpdr or trecpdr) |
| Symmetry of Propagation Delay of Receiver rising edge w.r.t. falling edge | trecsym | -2.0 | _ | 2.0 | μs | trecsym = max (trecpdf – trecpdr) Rrxd 2.4 k Ω to Vcc, Crxd 20 pF |
| Symmetry of Propagation Delay of Transmitter rising edge w.r.t. falling edge | ttranssym | -2.0 | _ | 2.0 | μs | ttranssym = max (ttranspdf - ttranspdr) |
| Bus dominant time-out time | t _{TO(LIN)} | | 25 | _ | mS | |
| Time to sample FAULT/TXE for bus conflict reporting | tFAULT | _ | _ | 32.5 | μs | tFAULT = max (tTRANSPD + tSLOPE + tRECPD) |
| Duty Cycle 1 @20.0 kbit/sec | | .396 | _ | | %tBIT | CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.744 x VBB, THDOM(MAX) = 0.581 x VBB, VBB =7.0V - 18V; tBIT = 50 μ S. D1 = tBUS_REC(MIN) / 2 x tBIT) |
| Duty Cycle 2 @20.0 kbit/sec | | _ | _ | .581 | %tBIT | CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.284 x VBB, THDOM(MAX) = 0.422 x VBB, VBB =7.6V - 18V; tBIT = 50 μ S. D2 = tBUS_REC(MAX) / 2 x tBIT) |
| Duty Cycle 3 @10.4 kbit/sec | | .417 | _ | | %tBIT | CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.778 x VBB, THDOM(MAX) = 0.616 x VBB, VBB =7.0V - 18V; tBIT = 96 μ S. D3 = tBUS_REC(MIN) / 2 x tBIT) |
| Duty Cycle 4 @10.4 kbit/sec | | _ | _ | .590 | %tвіт | CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.251 x VBB, THDOM(MAX) = 0.389 x VBB, VBB =7.6V - 18V; tBIT = 96 μ S. D4 = tBUS_REC(MAX) / 2 x tBIT) |

2.4 AC Specification (Continued)

| AC CHARACTERISTICS | VBB = 6.0V to | VBB = $6.0V$ to $18.0V$; TA = -40° C to $+125^{\circ}$ C | | | | | | |
|--|----------------------|--|------|------|-------|-----------------|--|--|
| Parameter | Sym. | Min. | Тур. | Max. | Units | Test Conditions | | |
| Voltage Regulator | | | | | | | | |
| Bus Activity Debounce time | t _{BDB} | 30 | 80 | 250 | μs | | | |
| Bus Activity to Voltage Regulator Enabled | t _{BACTIVE} | 35 | _ | 200 | μs | | | |
| Voltage Regulator Enabled to Ready | t _{VEVR} | 300 | _ | 1200 | μs | (Note 1) | | |
| Chip Select to Ready Mode | tcsr | _ | _ | 230 | μs | (Note 2) | | |
| Chip Select to Power-down | tcspd | _ | _ | 330 | μs | (Note 2) | | |
| Short circuit to shut-down | tshutdown | 20 | _ | 100 | μs | | | |
| RESET Timing | | | | | | | | |
| VREG OK detect to RESET inactive | trpu | _ | _ | 60 | μs | (Note 2) | | |
| VREG not OK detect to RESET active | tRPD | _ | _ | 60 | μs | (Note 2) | | |

Note 1: Time depends on external capacitance and load. Test condition: CREG = 4.7uF, no resistor load.

2.5 Thermal Specifications

| THERMAL CHARACTERISTICS | | | | | |
|-------------------------------|-----------|-------|------|-------|-----------------|
| Parameter | Symbol | Тур. | Max. | Units | Test Conditions |
| Recovery Temperature | θRECOVERY | +140 | _ | °C | |
| Shutdown Temperature | θSHUTDOWN | +150 | _ | °C | |
| Short Circuit Recovery Time | ttherm | 1.5 | 5.0 | ms | |
| Thermal Package Resistances | | | • | • | |
| Thermal Resistance, 8L-PDIP | θJA | 89.3 | _ | °C/W | |
| Thermal Resistance, 8L-SOIC | θJA | 149.5 | _ | °C/W | |
| Thermal Resistance, 8L-DFN | θJA | 48 | _ | °C/W | |
| Thermal Resistance, 14L-PDIP | θJA | 70 | _ | °C/W | |
| Thermal Resistance, 14L-SOIC | θJA | 95.3 | _ | °C/W | |
| Thermal Resistance, 14L-TSSOP | θЈА | 100 | _ | °C/W | |

Note 1: The maximum power dissipation is a function of TJMAX, Θ JA and ambient temperature T_A . The maximum allowable power dissipation at an ambient temperature is PD = (TJMAX - TA) Θ JA. If this dissipation is exceeded, the die temperature will rise above 150°C and the MCP2021A/2A will go into thermal shutdown.

^{2:} For design guidance only, not tested.

2.6 Timing Diagrams and Specifications

FIGURE 2-2: BUS TIMING DIAGRAM

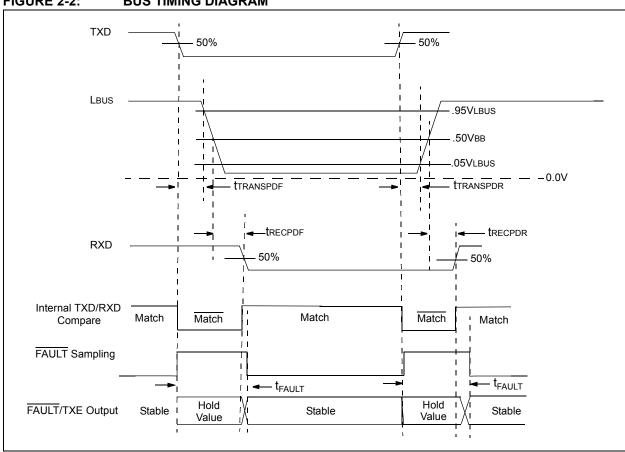


FIGURE 2-3: REGULATOR BUS WAKE TIMING DIAGRAM

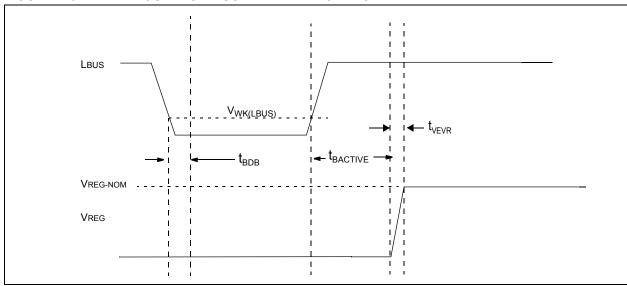


FIGURE 2-4: CS/LWAKE, REGULATOR AND RESET TIMING DIAGRAM

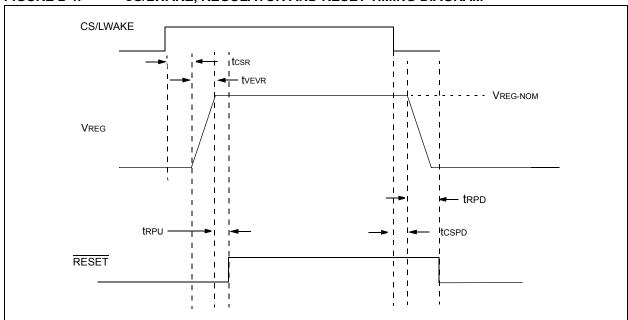


FIGURE 2-5: TYPICAL IBBQ VS. TEMPERATURE - 5.0V

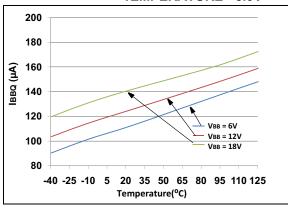


FIGURE 2-7: TYPICAL IPD VS. TEMPERATURE - 5.0V

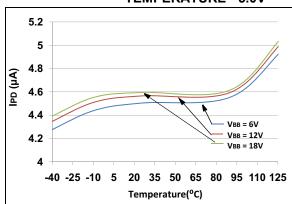


FIGURE 2-6: TYPICAL IBBTO VS. TEMPERATURE - 5.0V

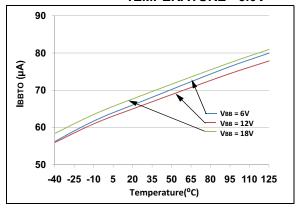


FIGURE 2-8: TYPICAL IBBQVS. TEMPERATURE - 3.3V

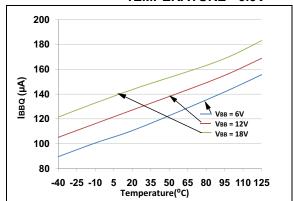


FIGURE 2-9: TYPICAL IBBTO VS. TEMPERATURE - 3.3V

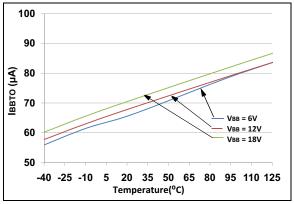
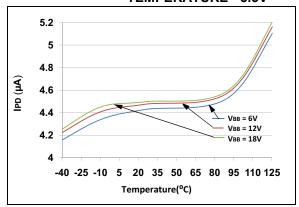


FIGURE 2-10: TYPICAL IPD VS. TEMPERATURE - 3.3V

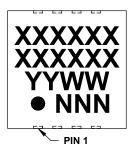


NOTES:

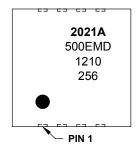
3.0 PACKAGING INFORMATION

3.1 Package Marking Information

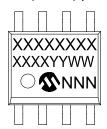
8-Lead DFN (4x4x0.9 mm) (MCP2021A)



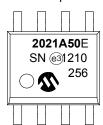
Example



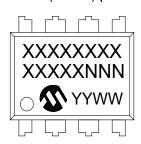
8-Lead SOIC (150 mil) (MCP2021A)



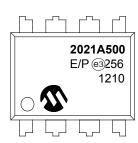
Example:



8-Lead PDIP (300 mil) (MCP2021A)



Example



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

e3 Pb-free JEDEC designator for Matte Tin (Sn)

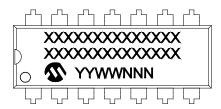
This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

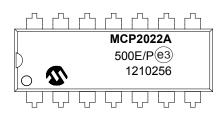
Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

Package Marking Information (Continued)

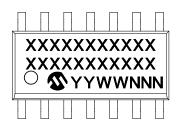
14-Lead PDIP (300 mil) (MCP2022A)



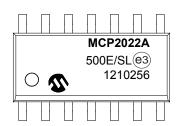
Example



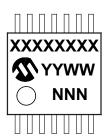
14-Lead SOIC (.150") (MC2022A)



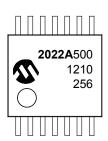
Example



14-Lead TSSOP (MCP2022A)



Example



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

(e3) Pb-free JEDEC designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (

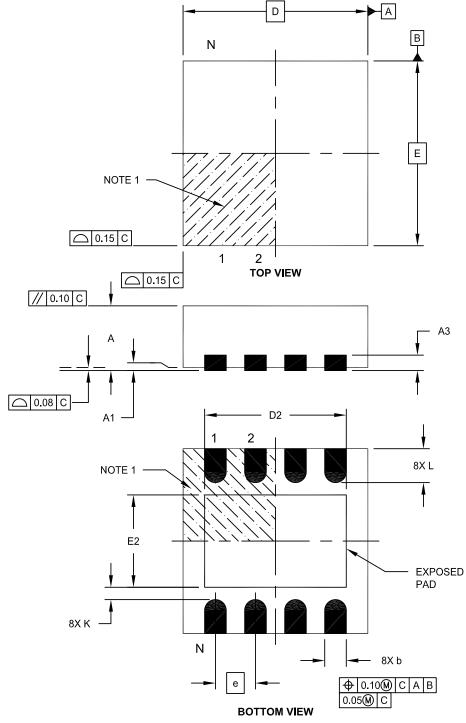
can be found on the outer packaging for this package.

lote: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available

characters for customer-specific information.

8-Lead Plastic Dual Flat, No Lead Package (MD) – 4x4x0.9 mm Body [DFN]

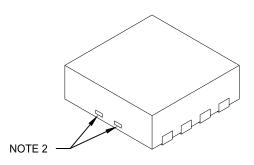
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-131E Sheet 1 of 2

8-Lead Plastic Dual Flat, No Lead Package (MD) - 4x4x0.9 mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| Units | | N | IILLIMETER | MAX | | |
|------------------------|----|----------|-------------------|------|--|--|
| Dimension Limits | | MIN | NOM | MAX | | |
| Number of Pins | N | 8 | | | | |
| Pitch | е | 0.80 BSC | | | | |
| Overall Height | Α | 0.80 | 0.90 | 1.00 | | |
| Standoff | A1 | 0.00 | 0.02 | 0.05 | | |
| Contact Thickness | A3 | 0.20 REF | | | | |
| Overall Length | D | 4.00 BSC | | | | |
| Exposed Pad Width | E2 | 2.60 | 2.70 | 2.80 | | |
| Overall Width | E | 4.00 BSC | | | | |
| Exposed Pad Length | D2 | 3.40 | 3.50 | 3.60 | | |
| Contact Width | b | 0.25 | 0.30 | 0.35 | | |
| Contact Length | Ĺ | 0.30 | 0.40 | 0.50 | | |
| Contact-to-Exposed Pad | K | 0.20 | - | - | | |

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated
- 4. Dimensioning and tolerancing per ASME Y14.5M

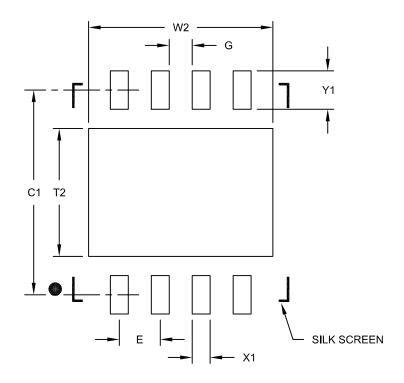
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-131E Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MD) - 4x4x0.9 mm Body [DFN]

Ste: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| | N | IILLIMETER | S | |
|----------------------------|----|-------------------|------|------|
| Dimension Limits | | MIN | NOM | MAX |
| Contact Pitch | E | 0.80 BSC | | |
| Optional Center Pad Width | W2 | | | 3.60 |
| Optional Center Pad Length | T2 | | | 2.50 |
| Contact Pad Spacing | C1 | | 4.00 | |
| Contact Pad Width (X8) | X1 | | | 0.35 |
| Contact Pad Length (X8) | Y1 | | | 0.75 |
| Distance Between Pads | G | 0.45 | | · |

Notes:

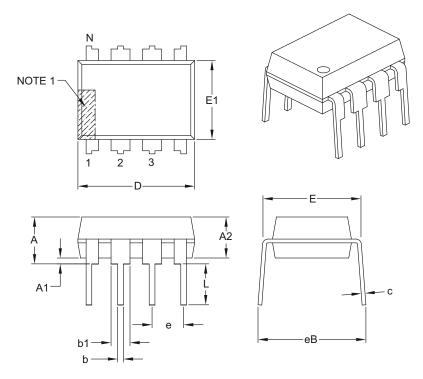
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2131C

8-Lead Plastic Dual In-Line (P) - 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| | Units | | INCHES | | | |
|----------------------------|------------------|----------|--------|------|--|--|
| | Dimension Limits | | NOM | MAX | | |
| Number of Pins | N | 8 | | | | |
| Pitch | е | .100 BSC | | | | |
| Top to Seating Plane | A | _ | _ | .210 | | |
| Molded Package Thickness | A2 | .115 | .130 | .195 | | |
| Base to Seating Plane | A1 | .015 | _ | _ | | |
| Shoulder to Shoulder Width | E | .290 | .310 | .325 | | |
| Molded Package Width | E1 | .240 | .250 | .280 | | |
| Overall Length | D | .348 | .365 | .400 | | |
| Tip to Seating Plane | L | .115 | .130 | .150 | | |
| Lead Thickness | С | .008 | .010 | .015 | | |
| Upper Lead Width | b1 | .040 | .060 | .070 | | |
| Lower Lead Width | b | .014 | .018 | .022 | | |
| Overall Row Spacing § | eB | _ | _ | .430 | | |

Notes:

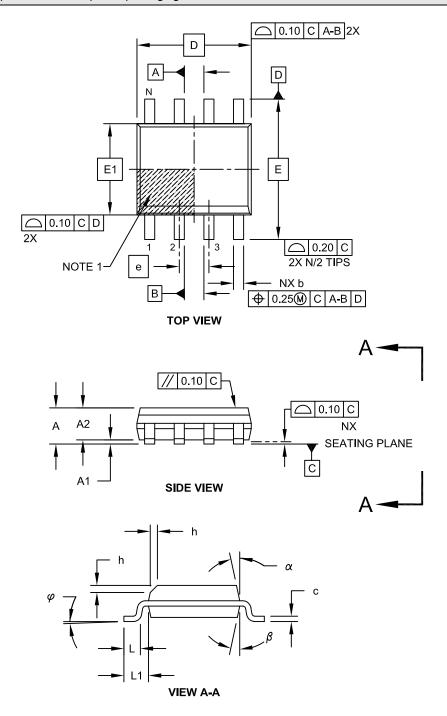
- 1. Pin 1 visual index feature may vary, but must be located with the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

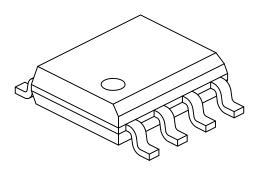
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| Units | | MILLIMETERS | | | |
|--------------------------|-----------|-------------|-----|------|--|
| Dimension Limits | | MIN | NOM | MAX | |
| Number of Pins | N | 8 | | | |
| Pitch | е | 1.27 BSC | | | |
| Overall Height | Α | 1 | i | 1.75 | |
| Molded Package Thickness | A2 | 1.25 | i | = | |
| Standoff § | A1 | 0.10 | i | 0.25 | |
| Overall Width | Е | 6.00 BSC | | | |
| Molded Package Width | E1 | 3.90 BSC | | | |
| Overall Length | D | 4.90 BSC | | | |
| Chamfer (Optional) | h | 0.25 | i | 0.50 | |
| Foot Length | L | 0.40 | i | 1.27 | |
| Footprint | L1 | 1.04 REF | | | |
| Foot Angle | φ | 0° | i | 8° | |
| Lead Thickness | С | 0.17 | i | 0.25 | |
| Lead Width | b | 0.31 | ı | 0.51 | |
| Mold Draft Angle Top | α | 5° | - | 15° | |
| Mold Draft Angle Bottom | β | 5° | - | 15° | |

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

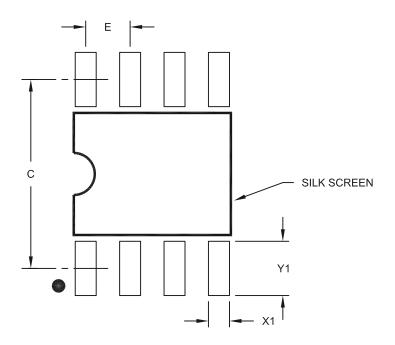
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| | Units MILLIMETERS | | | S |
|-------------------------|-------------------|----------|------|------|
| Dimension Limits | | MIN | NOM | MAX |
| Contact Pitch | Е | 1.27 BSC | | |
| Contact Pad Spacing | С | | 5.40 | |
| Contact Pad Width (X8) | X1 | | | 0.60 |
| Contact Pad Length (X8) | Y1 | | | 1.55 |

Notes:

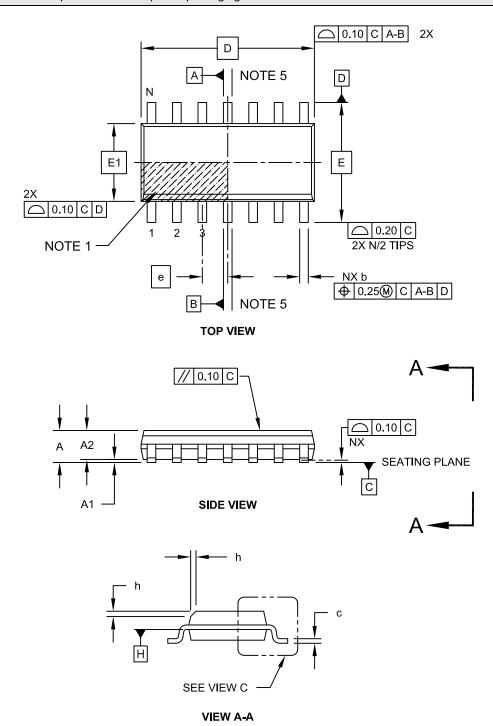
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

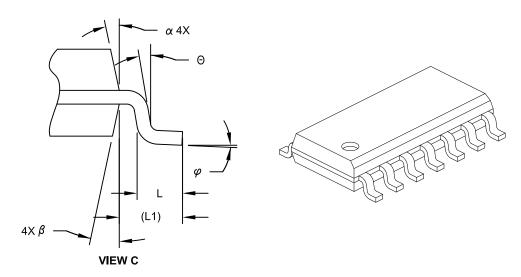
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-065C Sheet 1 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| Units | | MILLIMETERS | | |
|--------------------------|----|-------------|-----|------|
| Dimension Limits | | MIN | NOM | MAX |
| Number of Pins | N | 14 | | |
| Pitch | е | 1.27 BSC | | |
| Overall Height | Α | - | - | 1.75 |
| Molded Package Thickness | A2 | 1.25 | - | i |
| Standoff § | A1 | 0.10 | - | 0.25 |
| Overall Width | E | 6.00 BSC | | |
| Molded Package Width | E1 | 3.90 BSC | | |
| Overall Length | D | 8.65 BSC | | |
| Chamfer (Optional) | h | 0.25 - 0. | | 0.50 |
| Foot Length | L | 0.40 | - | 1.27 |
| Footprint | L1 | 1.04 REF | | |
| Lead Angle | Θ | 0° | - | = |
| Foot Angle | φ | 0° | - | 8° |
| Lead Thickness | С | 0.10 | - | 0.25 |
| Lead Width | b | 0.31 | - | 0.51 |
| Mold Draft Angle Top | α | 5° | - | 15° |
| Mold Draft Angle Bottom | β | 5° | - | 15° |

Notes

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

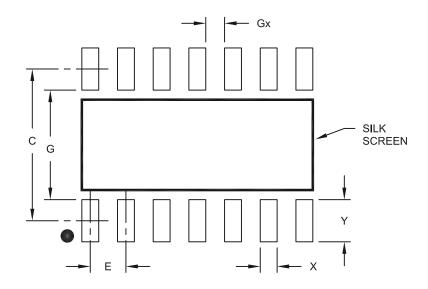
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| Units | | MILLIMETERS | | |
|-----------------------|--------|-------------|----------|------|
| Dimension | Limits | MIN | NOM | MAX |
| Contact Pitch | E | | 1.27 BSC | |
| Contact Pad Spacing | С | | 5.40 | |
| Contact Pad Width | Х | | | 0.60 |
| Contact Pad Length | Υ | | | 1.50 |
| Distance Between Pads | Gx | 0.67 | | |
| Distance Between Pads | G | 3.90 | | · |

Notes:

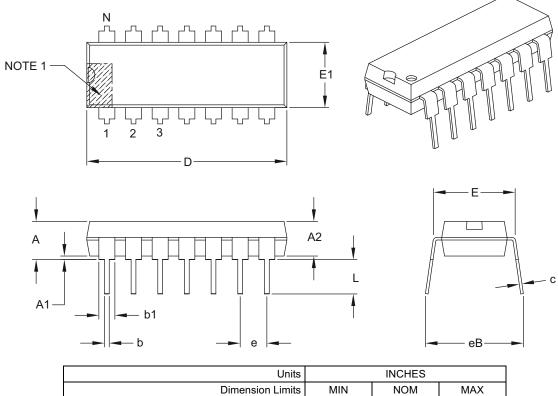
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

14-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| | Units | | INCHES | | |
|----------------------------|------------------|----------|--------|------|--|
| Dimensio | Dimension Limits | | NOM | MAX | |
| Number of Pins | N | 14 | | | |
| Pitch | е | .100 BSC | | | |
| Top to Seating Plane | Α | _ | _ | .210 | |
| Molded Package Thickness | A2 | .115 | .130 | .195 | |
| Base to Seating Plane | A1 | .015 | _ | _ | |
| Shoulder to Shoulder Width | Е | .290 | .310 | .325 | |
| Molded Package Width | E1 | .240 | .250 | .280 | |
| Overall Length | D | .735 | .750 | .775 | |
| Tip to Seating Plane | L | .115 | .130 | .150 | |
| Lead Thickness | С | .008 | .010 | .015 | |
| Upper Lead Width | b1 | .045 | .060 | .070 | |
| Lower Lead Width | b | .014 | .018 | .022 | |
| Overall Row Spacing § | eB | _ | _ | .430 | |

Notes:

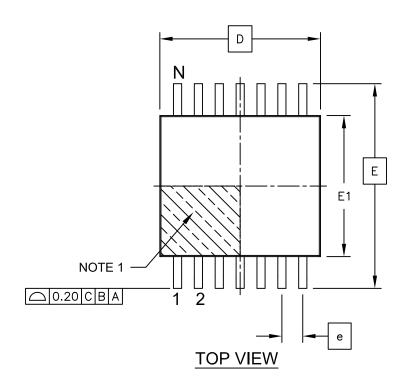
- 1. Pin 1 visual index feature may vary, but must be located with the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

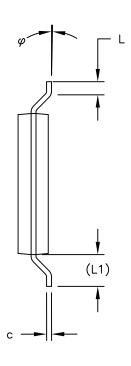
 ${\tt BSC: Basic \ Dimension. \ Theoretically \ exact \ value \ shown \ without \ tolerances.}$

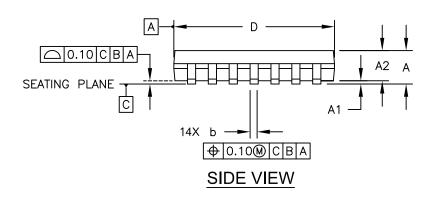
Microchip Technology Drawing C04-005B

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



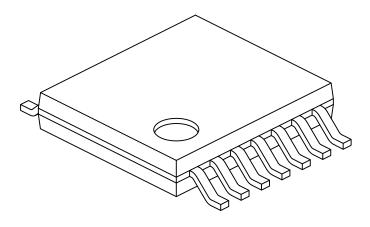




Microchip Technology Drawing C04-087C Sheet 1 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| Units | | MILLIMETERS | | | |
|--------------------------|------|-------------|------|------|--|
| Dimension Limits | | MIN | NOM | MAX | |
| Number of Pins | Ν | 14 | | | |
| Pitch | е | 0.65 BSC | | | |
| Overall Height | Α | İ | ı | 1.20 | |
| Molded Package Thickness | A2 | 0.80 | 1.00 | 1.05 | |
| Standoff | A1 | 0.05 | ı | 0.15 | |
| Overall Width | Е | 6.40 BSC | | | |
| Molded Package Width | E1 | 4.30 | 4.40 | 4.50 | |
| Molded Package Length | D | 4.90 | 5.00 | 5.10 | |
| Foot Length | L | 0.45 | 0.60 | 0.75 | |
| Footprint | (L1) | 1.00 REF | | | |
| Foot Angle | φ | 0° | - | 8° | |
| Lead Thickness | С | 0.09 | - | 0.20 | |
| Lead Width | b | 0.19 | - | 0.30 | |

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M

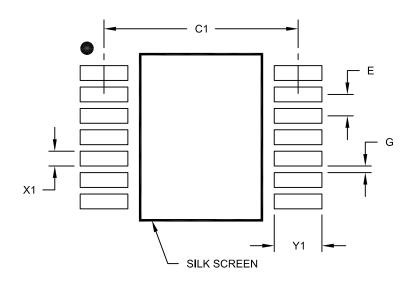
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| Units | | MILLIMETERS | | |
|--------------------------|----|-------------|----------|------|
| Dimension Limits | | MIN | NOM | MAX |
| Contact Pitch | Е | | 0.65 BSC | |
| Contact Pad Spacing | C1 | | 5.90 | |
| Contact Pad Width (X14) | | | | 0.45 |
| Contact Pad Length (X14) | Y1 | | | 1.45 |
| Distance Between Pads | G | 0.20 | | |

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

PRODUCT IDENTIFICATION SYSTEM

 $\underline{\text{To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.}\\$

| PART NO. | <u>-x</u> / <u>xx</u> | Exa | amples: |
|--------------------|---|----------------------|--|
| _ • | perature Package unge | a) b) c) | MCP2021A-330E/SL: 3.3V, 8L-SOIC package MCP2021A-330E/P: 3.3V, 8L-PDIP package MCP2021A-500E/SL: 5.0V, 8L-SOIC package |
| Device: | MCP2021A: LIN Transceiver with Voltage Regulator MCP2021AT: LIN Transceiver with Voltage Regulator (Tape and Reel) (SOIC only) | d) e) f) | MCP2021A-500E/P: 5.0V, 8L-PDIP package MCP2021AT-330E/SL: Tape and Reel, 3.3V, 8L-SOIC package MCP2021AT-500E/SL: Tape and Reel, 5.0V, 8L-SOIC package |
| Temperature Range: | E = -40°C to +125°C | g) h) | MCP2022A-330E/SL: 3.3V, 14L-SOIC package MCP2022A-330E/P: 3.3V, 14L-PDIP package |
| Package: | MD = Plastic Dual Flat DFN, 8-lead SN = Plastic Small Outline SOIC, 8-lead P = Plastic DIP (300 mil Body), 8-lead, 14-lead SL = Plastic SOIC, (150 mil Body), 14-lead ST = Plastic TSSOP, 14-lead | i) j) k) l) | MCP2022A-500E/SL: 5.0V, 14L-SOIC package MCP2022A-500E/P: 5.0V, 14L-PDIP package MCP2022AT-330E/SL: Tape and Reel, 3.3V, 14L-SOIC package MCP2022AT-500E/SL: Tape and Reel, 5.0V, 14L-SOIC package |

MCP2021A/2A

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (March 2012)

• Original Release of this Document.

MCP2021A/2A

NOTES:

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- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
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 MCP2021AT-330E/MD
 MCP2021AT-330E/SN
 MCP2021AT-500E/MD
 MCP2022A-330E/ST
 MCP2022A-500E/SL

 MCP2022A-500E/ST
 MCP2022AT-330E/SL
 MCP2022AT-330E/ST
 MCP2022AT-500E/SL
 MCP2022AT-500E/SL

 MCP2021A-330E/MD
 MCP2021A-500E/SN
 MCP2021AT-500E/SN
 MCP2021AT-500E/SN
 MCP2021A-500E/MD
 MCP2022A-330E/SL